

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
20V	38mΩ @ V _{GS} = 4.5V	4.8A
	45mΩ @ V _{GS} = 2.5V	4.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

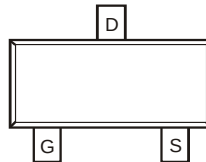
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

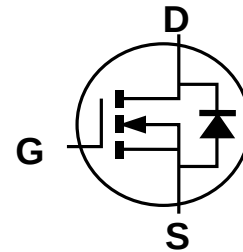
SOT23



Top View



Top View



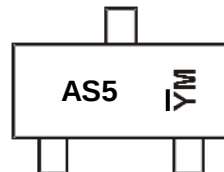
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2055U-7	SOT23	3,000/Tape & Reel
DMN2055U-13	SOT23	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



AS5 = Product Type Marking Code
YM = Date Code Marking
Y = Last Digit of Year (ex: 8 = 2018)
M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6)	Steady State	T _A = +25°C	I _D	4.8	A
		T _A = +85°C		3.8	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	162	°C/W
Total Power Dissipation (Note 6)		P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	113	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	28	38	mΩ	V _{GS} = 4.5V, I _D = 3.6A
			32	45		V _{GS} = 2.5V, I _D = 3.1A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	400	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	55	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	37	—	pF	
Gate Resistance	R _G	—	3.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	4.3	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6A
Gate-Source Charge	Q _{GS}	—	0.3	—	nC	
Gate-Drain Charge	Q _{GD}	—	4.8	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	2.8	—	ns	V _{DD} = 10V, V _{GS} = 5V, R _L = 1.7Ω, R _G = 6Ω
Turn-On Rise Time	t _R	—	2.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	15.4	—	ns	
Turn-Off Fall Time	t _F	—	4.4	—	ns	
Reverse Recovery Time	t _{RR}	—	6.8	—	ns	I _F = 1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	1.2	—	nC	I _F = 1.0A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

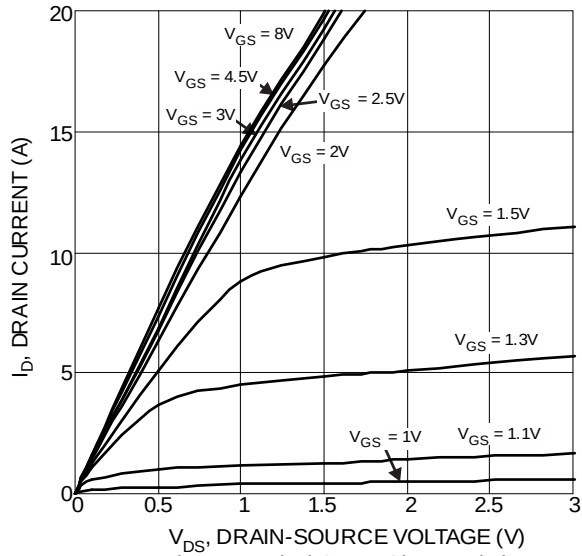


Figure 1 Typical Output Characteristic

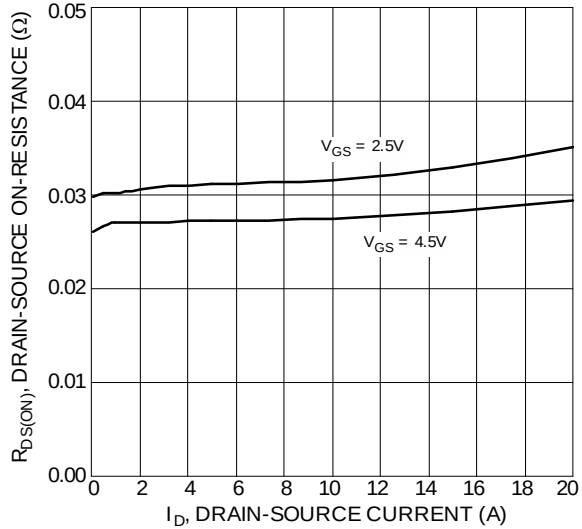


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

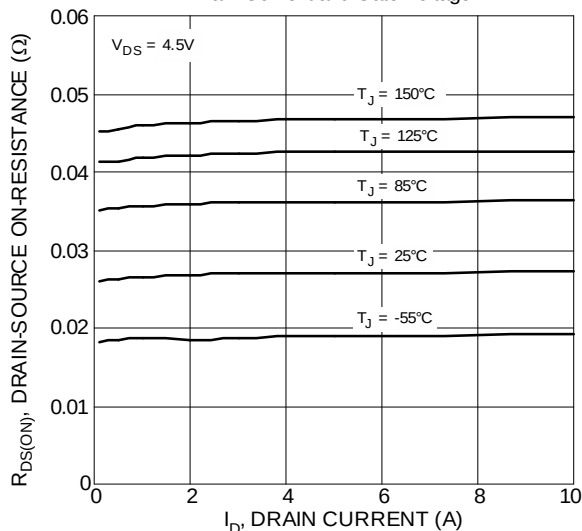


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

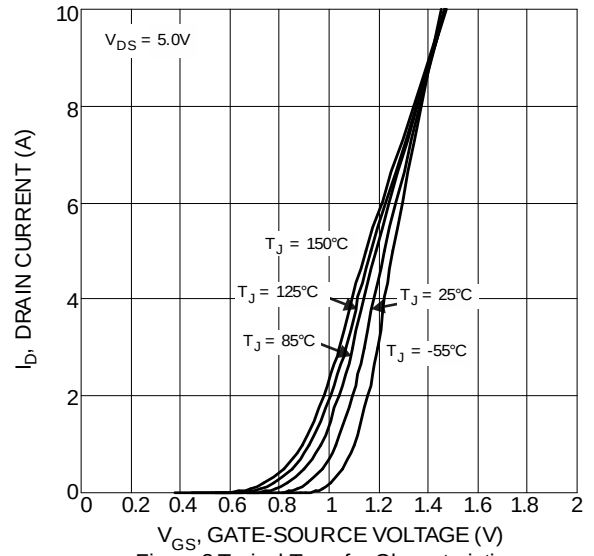


Figure 2 Typical Transfer Characteristics

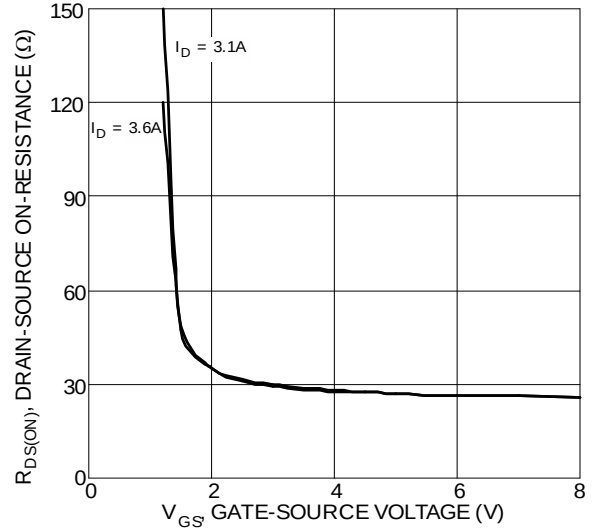


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

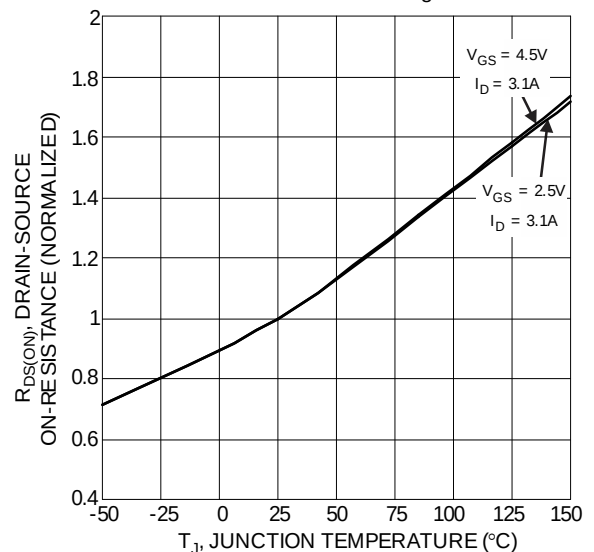


Figure 6 On-Resistance Variation with Temperature

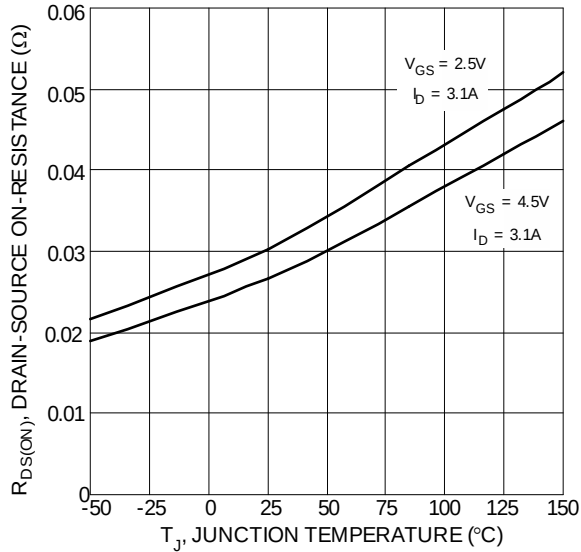


Figure 7 On-Resistance Variation with Temperature

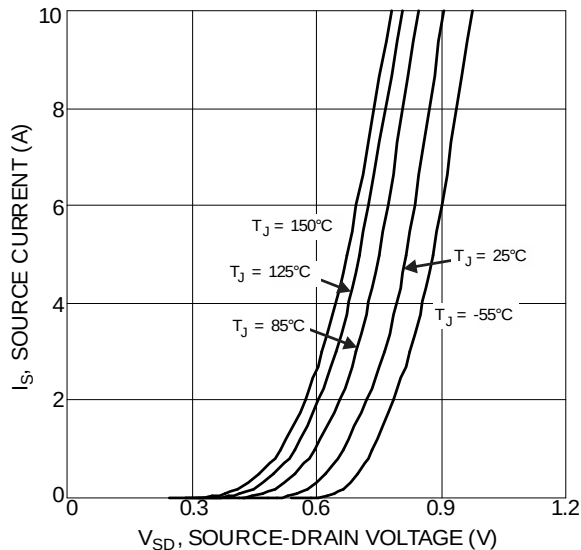


Figure 9 Diode Forward Voltage vs. Current

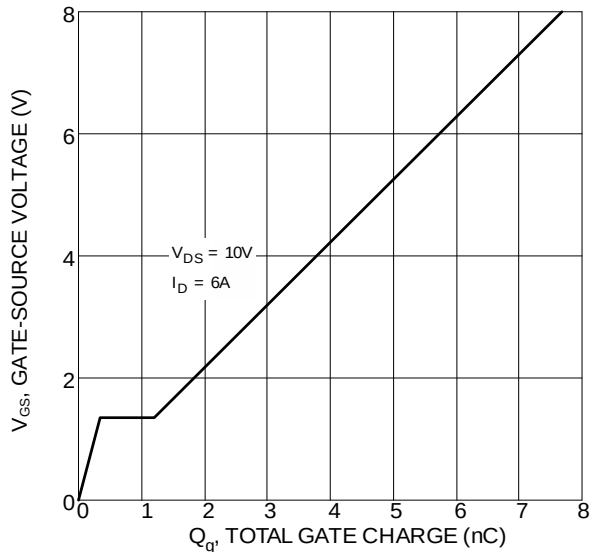


Figure 11 Gate Charge

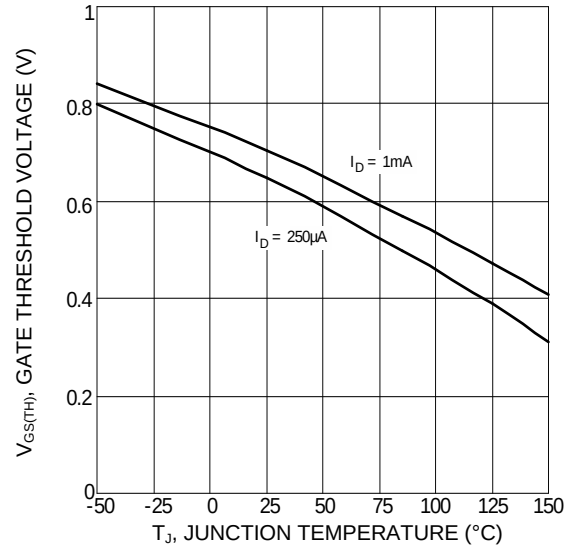


Figure 8 Gate Threshold Variation vs. Junction Temperature

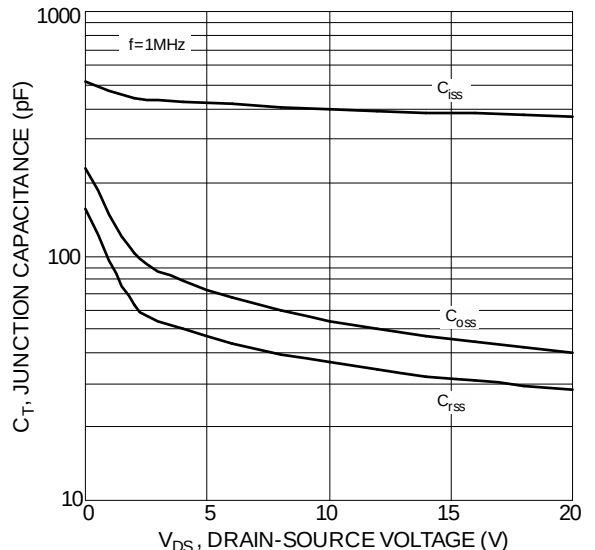


Figure 10 Typical Junction Capacitance

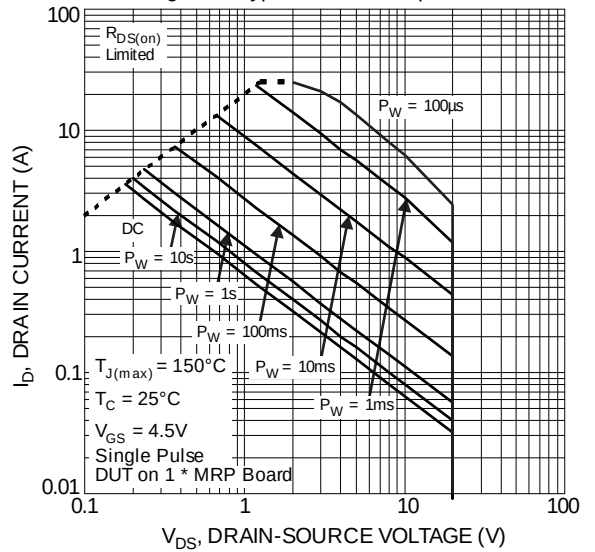
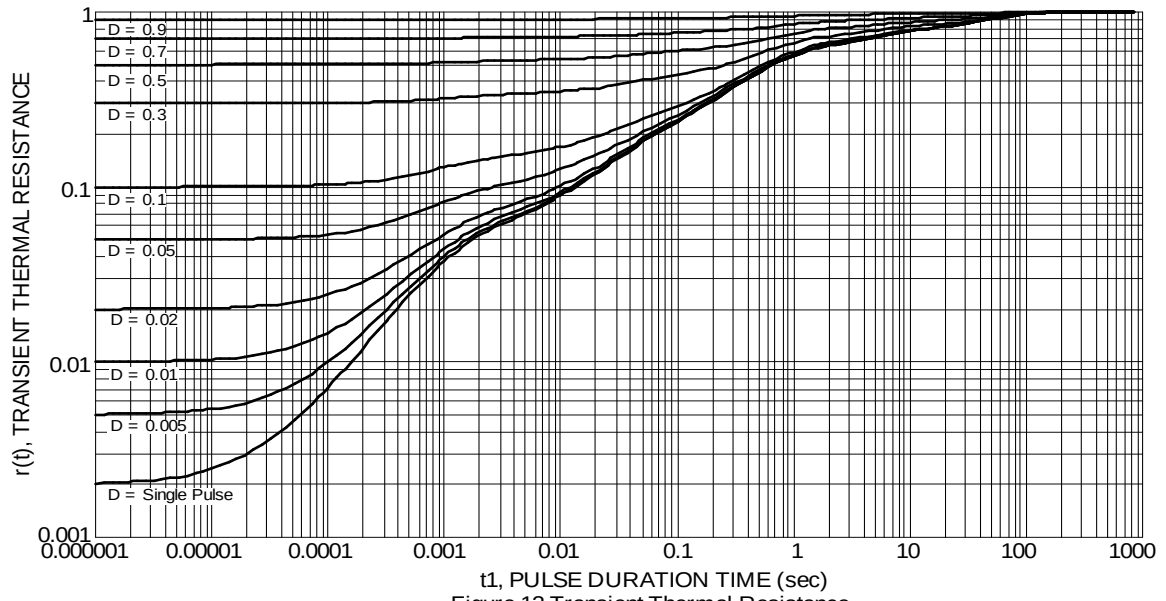


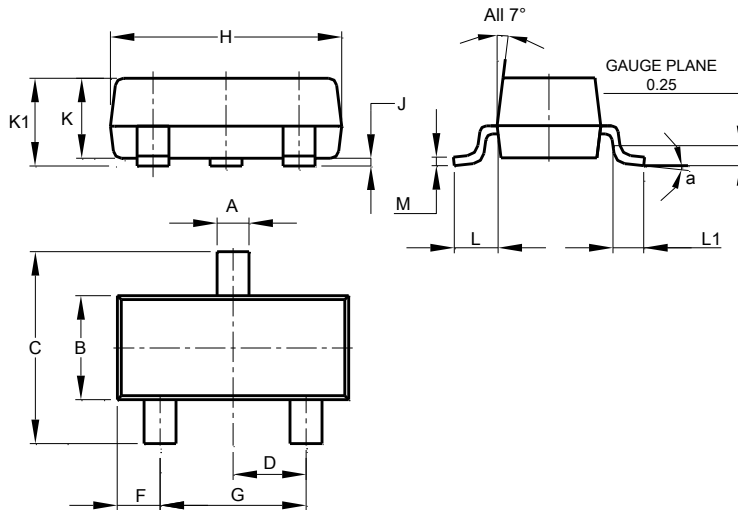
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

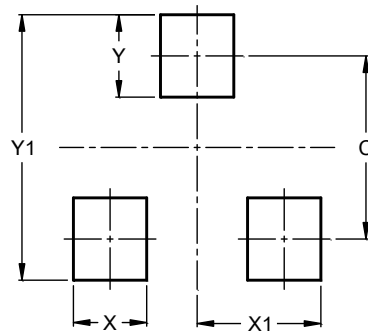


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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